MJ2955 (See 2N3055) MJ2955A (See 2N3055A)

## Medium-Power Complementary Silicon Transistors

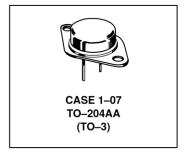
 $\ldots$  for use as output devices in complementary general purpose amplifier applications.

- High DC Current Gain hFE = 4000 (Typ) @ IC = 5.0 Adc
- · Monolithic Construction with Built-in Base-Emitter Shunt Resistors

# MJ2500 MJ2501\* MJ3000 MJ3001\*

\*Motorola Preferred Device

10 AMPERE
DARLINGTON
POWER TRANSISTORS
COMPLEMENTARY
SILICON
60-80 VOLTS
150 WATTS



#### **MAXIMUM RATINGS**

Rating	Symbol	MJ2500 MJ3000	MJ2501 MJ3001	Unit
Collector-Emitter Voltage	VCEO	60	80	Vdc
Collector-Base Voltage	V <sub>CB</sub>	60 80		Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5.0		Vdc
Collector Current	IC	10		Adc
Base Current	lΒ	0.2		Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	150 0.857		Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +200		°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θЈС	1.17	°C/W

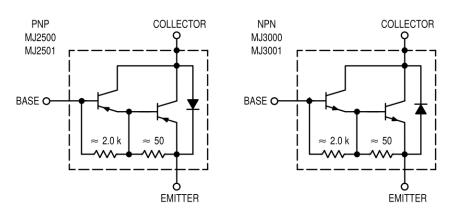


Figure 1. Darlington Circuit Schematic

Preferred devices are Motorola recommended choices for future use and best overall value.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic			Min	Max	Unit
OFF CHARACTERISTICS				•	•
Collector Emitter Breakdown Voltage <sup>(1)</sup> (IC = 100 mAdc, I <sub>B</sub> = 0)	MJ2500, MJ3000 MJ2501, MJ3001	V <sub>(BR)</sub> CEO	60 80	_	Vdc
Collector-Emitter Leakage Current (VEB = 60 Vdc, RBE = 1.0 k ohm) (VEB = 80 Vdc, RBE = 1.0 k ohm) (VEB = 60 Vdc, RBE = 1.0 k ohm, T <sub>C</sub> = 150°C) (VEB = 80 Vdc, RBE = 1.0 k ohm, T <sub>C</sub> = 150°C)	MJ2500, MJ3000 MJ2501, MJ3001 MJ2500, MJ3000 MJ2501, MJ3001	<sup>I</sup> CER		1.0 1.0 5.0 5.0	mAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)		IEBO	_	2.0	mAdc
Collector Emitter Leakage Current         (V <sub>CE</sub> = 30 Vdc, I <sub>B</sub> = 0)         MJ2500, MJ3000           (V <sub>CE</sub> = 40 Vdc, I <sub>B</sub> = 0)         MJ2501, MJ3001		ICEO	_	1.0 1.0	mAdc
ON CHARACTERISTICS <sup>(1)</sup>					
DC Current Gain (I <sub>C</sub> = 5.0 Adc, V <sub>CE</sub> = 3.0 Vdc)		hFE	1000	_	_

DC Current Gain (I <sub>C</sub> = 5.0 Adc, V <sub>CE</sub> = 3.0 Vdc)	hFE	1000		
Collector–Emitter Saturation Voltage ( $I_C = 5.0$ Adc, $I_B = 20$ mAdc) ( $I_C = 10$ Adc, $I_B = 50$ mAdc)	V <sub>CE(sat)</sub>		2.0 4.0	Vdc
Base Emitter Voltage (I <sub>C</sub> = 5.0 Adc, V <sub>CE</sub> = 3.0 Vdc)	V <sub>BE(on)</sub>	1	3.0	Vdc

<sup>(1)</sup>Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

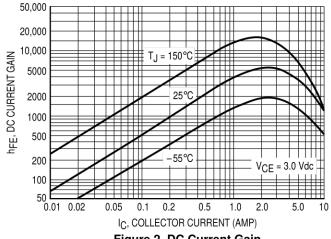


Figure 2. DC Current Gain

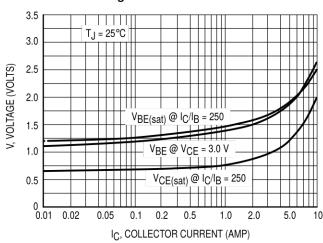


Figure 4. "On" Voltages

There are two limitations on the power handling ability of a transistor: junction temperature and secondary breakdown. Safe operating area curves indicate IC - VCE limits of the transistor that must be observed for reliable operation; e.g., the transistor must not be subjected to greater dissipation

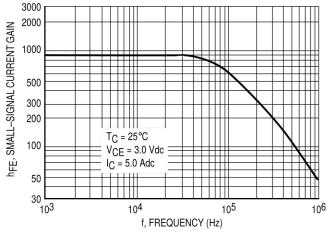


Figure 3. Small-Signal Current Gain

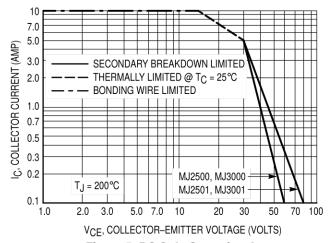
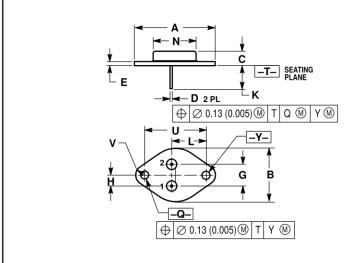


Figure 5. DC Safe Operating Area

than the curves indicate.

At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by secondary breakdown.

### **PACKAGE DIMENSIONS**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.550 REF		39.37 REF		
В		1.050		26.67	
С	0.250	0.335	6.35	8.51	
D	0.038	0.043	0.97	1.09	
Е	0.055	0.070	1.40	1.77	
G	0.430 BSC		10.92 BSC		
Н	0.215	BSC	5.46 BSC		
K	0.440	0.480	11.18	12.19	
L	0.665	BSC	16.89	BSC	
N	_	0.830		21.08	
Q	0.151	0.165	3.84	4.19	
U	1.187 BSC		30.15	BSC	
V	0.131	0.188	3.33	4 77	

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

**CASE 1-07** TO-204AA (TO-3) **ISSUE** Z

#### MJ2500 MJ2501 MJ3000 MJ3001

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